

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

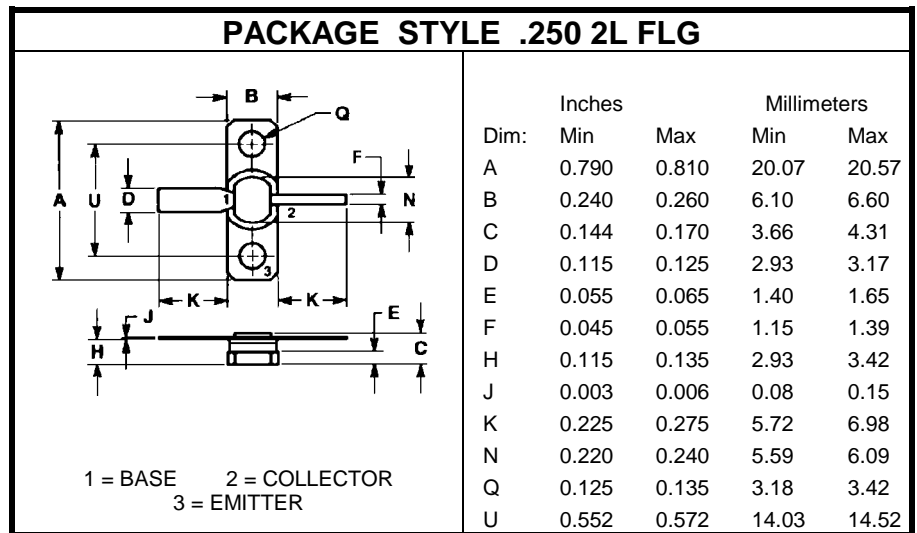
The **ASI LTE21009R** is Designed for Class A, Common Emitter Applications up to 2.5 GHz.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	250 mA
V_{CBO}	40 V
P_{DISS}	4.0 W @ $T_C \leq 75^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{ST}	-65°C to $+200^\circ\text{C}$
θ_{JC}	36 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0\text{ mA}$	40			V
BV_{CEO}	$I_C = 10\text{ mA}$	16			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.0			V
I_{CBO}	$V_{EB} = 1.5\text{ V}$			200	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 150\text{ mA}$	15		150	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			3.0	pF
G_P	$V_{CE} = 16\text{ V}$ $I_C = 150\text{ mA}$ $f = 2.1\text{ GHz}$	10			dB
P_{OUT}		0.6			W